

# S-Band, GaN/SiC, RF Power Transistor

2.7 - 2.9 GHz | 315 W typ | 60% Efficiency typ | 11dB Gain typ | 50 V | 300µs Pulse Length, 10% Duty Cycle

IGN2729M250C and IGN2729M250CS are high power GaN-on-SiC RF power transistors that have been designed to suit the unique needs of modern radar systems. They supply a minimum of 250W of peak output power, with typically >11 dB of gain and 60% efficiency. They operate from a 50 V supply voltage. For optimal thermal efficiency, the transistors are housed in a metal-based package with an epoxy-sealed ceramic lid.



## FEATURES

- GaN on SiC HEMT Technology
- Output Power >250W
- Pre-matched Input and Output Impedances
- High Efficiency - 60% typical
- 100% RF Tested Under 300µs, 10% duty cycle pulse conditions
- RoHS and REACH Compliant

## APPLICATIONS

- S-band Radar Systems

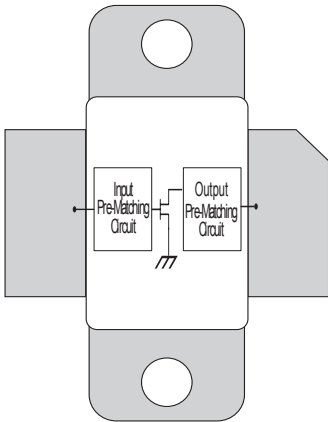


Table 1. RF Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
RF Output Power	$P_{OUT\ RF}$	250	315	396	W	$P_{IN} = 25W$ $f = 2.7, 2.8, 2.9\ GHz$ 300µs pulse length, 10% duty cycle $V_{DS} = 50V, I_{DQ} = 100mA$
Gain	G	10	11	12	dB	
Drain Efficiency	$\eta$	53	60	75	%	
Pulse Droop	D	-0.5	-0.1	+0.3	dB	
Input Return Loss	IRL	9	10	18	dB	
Load Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	3:1				

Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

Table 2. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	$V_{DS}$	120	V	25 °C
DC Gate-Source Voltage	$V_{GS}$	-5 to +1.0	V	25 °C
DC Drain Current	$I_D$	36	A	25 °C
DC Gate Current	$I_G$	36	mA	25 °C
RF Input Power	$P_{RF,IN}$	25	W	25 °C
Operating Channel Temperature	$T_{CH}$	-55 to +225	°C	
Storage Temperature	$T_{STG}$	-55 to +150	°C	
Soldering Temperature	$T_{SOLDER}$	260 for 60s	°C	

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 3. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gate Pinch-Off Voltage	$V_P$	-5.0			V	$V_{DS} = 50V, I_{DS} = 1mA$
Quiescent Gate Voltage	$V_Q$		-3.5		V	$V_{DS} = 50V, I_{DQ} = 100mA$

Table 4. Test Fixture Source & Load Impedances (Case temperature = 25 °C unless otherwise stated)

Frequency (GHz)	$Z_{IF}$	$Z_{OF}$	Units	Test Conditions
2.7	3.7 - j 5.9	3.8 - j 8.6	$\Omega$	$P_{OUT} = 250W$ 300 $\mu s$ Pulse length, 10% Duty Cycle $V_{DS} = 50V, I_{DQ} = 100mA$
2.8	3.0 - j 5.6	3.6 - j 8.2	$\Omega$	
2.9	2.4 - j 5.3	3.4 - j 7.6	$\Omega$	

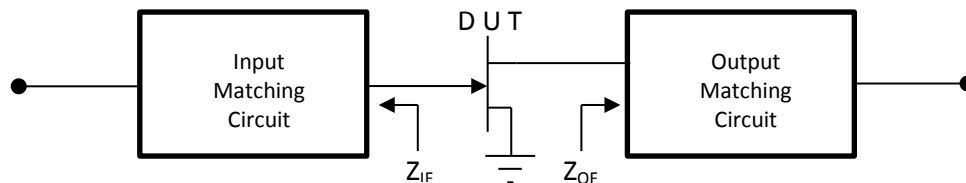
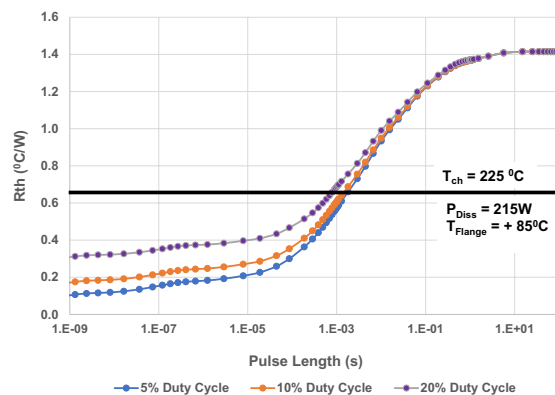


Table 5. Thermal Resistance (Case temperature = 85 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Peak Thermal Resistance, Channel to Case	$R_{TH}$		0.45		°C/W	$P_{DISS} = 215W$ 300 $\mu s$ pulse length, 10% duty cycle $V_{DS} = 50V$



TYPICAL PERFORMANCE

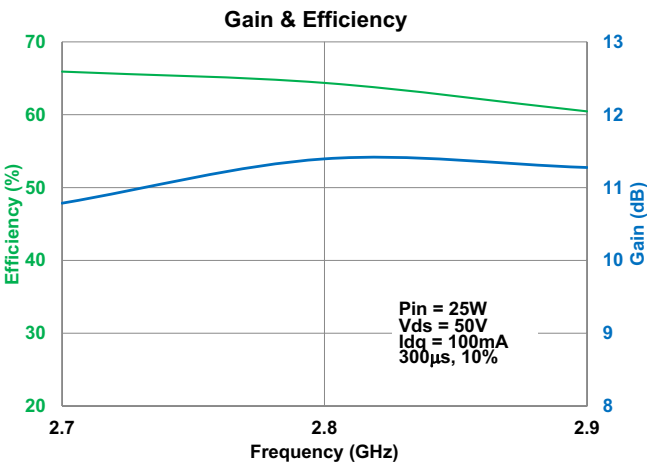


Figure 1

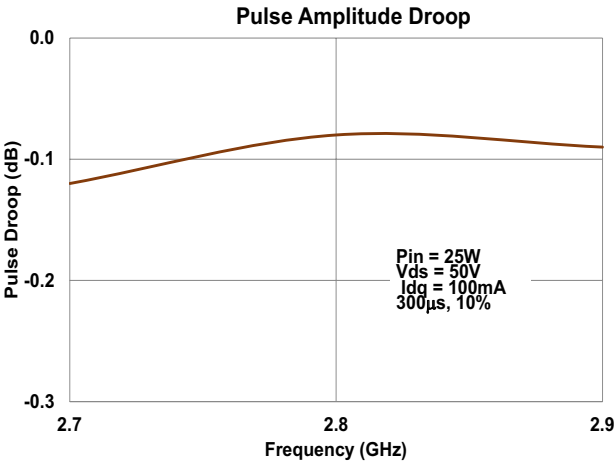
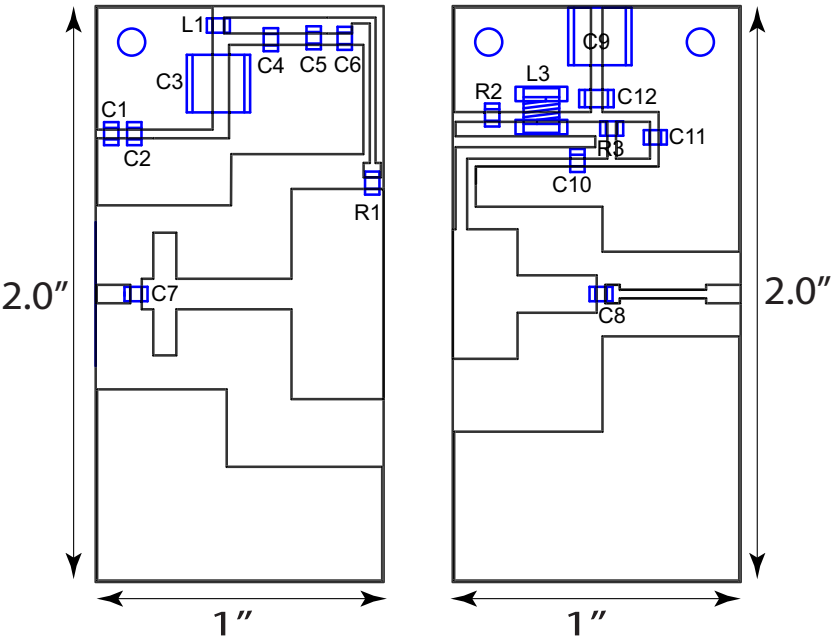


Figure 2

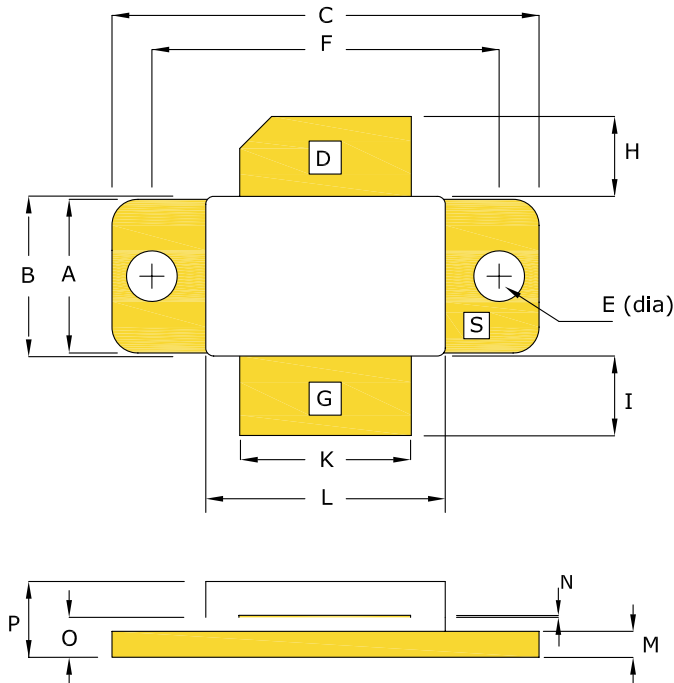
TEST FIXTURE



Bill of Materials for IGN2729M250C Test Fixture

Designator	Description	Quantity	Part Number
C1, C4, C11	CAP 0.1μF, 0805 100V	3	08051C104K4T2A
C2, C5, C6	CAP 27pF, 0805, 100V	3	ATC600F270
C3 ,C9	CAP 10μF, 2220, X7R 50V	2	22201C106MAT2A
C7, C8	CAP 12pF, Edge Mount	2	ATC600F120
C10	CAP 5.6pF, Edge Mount	1	ATC600F5R6
C12	CAP 1μF, 1206, 100V	1	12061C105K4T2A
L1, L2	IND FB, 120 OHM, 0805 5A	2	ILHB0805ER121V
L3	IND 5N5, 1508	1	1508-5N5JLB
R1, R2, R3, R4	RES, 5R1, 0805	4	ERJ-6GEYJ5R1V
PC Board Type	ROGERS RO4350B-03011, 30mil, 1/1oz. Copper	2	

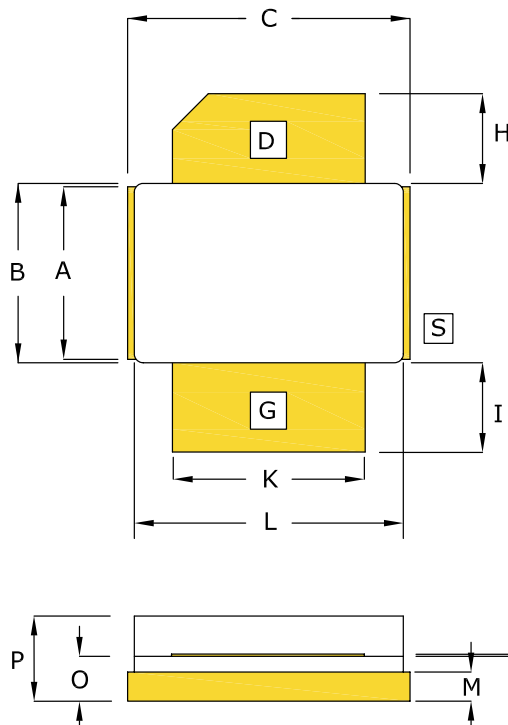
### PACKAGE PL64A1



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.380	0.390		
B	0.395	0.405		
C	1.065	1.075	27.05	27.31
E	0.124	0.130	3.15	3.30
F	0.865	0.875	21.97	22.23
H	0.190	0.223	4.83	5.66
I	0.190	0.223	4.83	5.66
J	--	--	--	--
K	0.425	0.435	10.80	11.05
L	0.595	0.605	15.11	15.37
M	0.060	0.070	1.52	1.78
N	0.004	0.006	0.10	0.15
O	0.096	0.106	2.44	2.69
P	0.181	0.214	4.60	5.44

PIN SCHEDULE	
D	DRAIN
S	SOURCE
G	GATE

### BOLT-DOWN FLANGE OPTION IGN2729M250C



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.380	0.390	9.65	9.91
B	0.395	0.405	10.03	10.29
C	0.625	0.635	15.88	16.13
E	--	--	--	--
F	--	--	--	--
H	0.190	0.223	4.83	5.66
I	0.190	0.223	4.83	5.66
J	--	--	--	--
K	0.425	0.435	10.80	11.05
L	0.595	0.605	15.11	15.37
M	0.060	0.070	1.52	1.78
N	0.004	0.006	0.10	0.15
O	0.096	0.106	2.44	2.69
P	0.181	0.214	4.60	5.44

PIN SCHEDULE	
D	DRAIN
S	SOURCE
G	GATE

### EARLESS FLANGE OPTION IGN2729M250CS

### ESD & MSL Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivity Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

### RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

### REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

### Disclaimer

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#### DEFINITIONS:

##### DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

**MAXIMUM RATINGS** Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.